

EM520 1.0AMP. HIGH VOLTAGE SILICON RECTIFIER DO-41 FEATURE . High current capability, . Low forward voltage drop . Low power loss, high efficiency .110(2.8) DIA. .787(20.0). High surge capability MÌN. .080(2.0). High voltage . High temperature soldering guaranteed +.205(5.2) 260°C /1 0sec/0.375" lead length at 5 lbs tension .166(4.2)**MECHANICAL DATA** .032(0.8) DIA. .787(20.0) .025(0.65). Terminal: Plated axial leads solderable per MIN. MIL-STD 202E, method 208C . Case: Molded with UL-94 Class V-0 recognized Flame Retardant Epoxy . Polarity: color band denotes cathode Dimensions in inches and (millimeters) . Mounting position: any MAXIMUM RATINGS AND ELECTRONICAL CHARACTERISTICS (Ratings at 25°C ambient temperature unless otherwise specified.Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%)

Type Number	SYM BOL	EM520	units
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	2000	V
Maximum RMS Voltage	V _{RMS}	1400	V
Maximum DC Blocking Voltage	V _{DC}	2000	V
Maximum Average Forward rectified Current at $T_A=50^{\circ}C$	IF(AV)	1.0	А
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rate load (JEDEC method)	IFSM	30	А
Maximum Forward Voltage Drop per element at 1.0 DC	V _F	1.1	V
Maximum DC Reverse Current @ T _A =25°C	I_R	5.0	μΑ
at Rated DC Blocking Voltage @ T _A =100°C		500	
I ² t Rating for Fusing (t < 8.3ms)	<i>I</i> ² t	3.735	A ² Sec
Typical Junction Capacitance (Note1)	CJ	15	pF
Typical Thermal Resistance (Note 2)	R _(JA)	40	°C/W
Storage Temperature Range	T _{STG}	-55 to +150	°C
Operation Temperature Range	T_J	-55 to +150	°C

Note:

1. Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc

2. Thermal Resistance from Junction to Ambient at 0.375" (9.5mm) lead length



RATING AND CHARACTERISTIC CURVES (EM520)

